

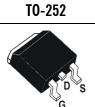
DG100N03D100V N-Channel Power MOSFET

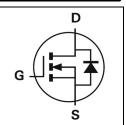
DG-FET Power MOSFET

 V_{DSS} , 100V

 $R_{DS(0N)}$, $9.6m\Omega$ (max.) @ $V_{GS}{=}10V$ $R_{DS(0N)}$, $12.5m\Omega$ (max.) @ $V_{GS}{=}4.5V$

 I_D , 71A





Description

The DG100N03D uses advanced DG-FET $^{\text{TM}}$ technology and designs to provide excellent $R_{\text{DS(0N)}}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

- · Low On-Resistance
- Low Input Capacitance
- · Low Miller Charge
- Low Input/Output Leakage

Applications

- Lithium-Ion Secondary Batteries
- Load Switch
- DC-DC converters and Off-line UPS

Ordering Information

| Ordering Code | RoHS Status | Package | Package Code | Packing | Quantity |
|---------------|--------------|---------|--------------|-------------|----------|
| DG100N03D | Halogen-Free | T0-252 | D | Tape & Reel | 3,000 |

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

| Parameter | | Symbol | Value | Unit |
|--|----------------------|------------------|---------------|------|
| Drain-Source Voltage | | V _{DS} | 100 | ٧ |
| Gate-Source Voltage | | V_{GS} | ±25 | ٧ |
| Drain Current-Continuous | T _C =25°C | | 71 | А |
| T_c =100°C | | ID | 45 | А |
| Drain Current-Pulsed Note 1 | I _{DM} | 170 | Α | |
| Avalanche Current | | I _{AS} | 18 | А |
| Avalanche Energy, L=0.1mH | | E _{AS} | 16.2 | mJ |
| T _c =25°C | | D | 104 | W |
| Maximum Power Dissipation $T_c = 100^{\circ}C$ | | P _D | 41 | W |
| Storage Temperature Range | | T _{STG} | -55 to +150 | °C |
| Operating Junction Temperature Range | | T _J | -55 to +150 | °C |

Thermal Resistance Ratings

| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit |
|------------------------------------|-------------------|--------------|------|------|------|------|
| Maximum Junction-to-Ambient Note 2 | $R_{\theta_{JA}}$ | Steady State | - | - | 50 | °C/W |
| Maximum Junction-to-Case | $R_{\Theta JC}$ | Steady State | - | - | 1.2 | °C/W |

1



Electrical Characteristics ($T_{_J}$ =25°C unless otherwise noted)

| OFF CHARACTERISTICS | | | | | | | |
|---------------------------------|------------------|-----------------------------------|------|------|------|------|--|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_{DS} = 250 \mu A$ | 100 | - | - | V | |
| Zero Gate Voltage Drain Current | I _{DSS} | V_{DS} =80V, V_{GS} =0V | - | - | 1 | μA | |
| Gate-Body Leakage | I _{GSS} | $V_{GS} = \pm 25V, V_{DS} = 0V$ | - | - | ±100 | nA | |

| ON CHARACTERISTICS | | | | | | |
|----------------------------------|---------------------|---------------------------------------|------|------|------|------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{DS} = V_{GS}, I_{DS} = 250 \mu A$ | 1.0 | - | 2.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | $V_{GS}=10V$, $I_{DS}=18A$ | - | 7.8 | 9.6 | mΩ |
| Drain-Source On-State Resistance | R _{DS(ON)} | $V_{GS} = 4.5V, I_{DS} = 10A$ | - | 9.5 | 12.5 | mΩ |

| DYNAMIC CHARACTERISTICS | | | | | | | |
|------------------------------|------------------|---------------------------------------|------|------|------|------|--|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit | |
| Input Capacitance | C _{iss} | | - | 2048 | - | | |
| Output Capacitance | C _{oss} | $V_{DS}=50V$, $V_{GS}=0V$, $f=1MHz$ | - | 684 | - | pF | |
| Reverse Transfer Capacitance | C _{rss} | | - | 7 | - | | |
| Gate Resistance | R_{g} | $V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$ | - | 0.5 | 0.9 | Ω | |

| SWITCHING CHARACTERISTICS | | | | | | |
|-------------------------------|----------------|---|------|------|------|------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit |
| Turn-On Delay Time | $T_{d(on)}$ | | - | 7.6 | - | |
| Rise Time | t _r | V FOV V 10V D 20 | - | 2.7 | - | |
| Turn-Off Delay Time | $T_{d(off)}$ | V_{DS} =50V, V_{GS} =10V, R_{GEN} =3 Ω | - | 23.5 | - | ns |
| Fall Time | t _f | | - | 3.5 | - | |
| Total Gate Charge at 4.5V | $Q_{\rm g}$ | | - | 13 | - | |
| Gate to Source Gate Charge | Q_{gs} | $V_{DS} = 50V$, $I_{DS} = 13A$, $V_{GS} = 4.5V$ | - | 6 | - | nC |
| Gate to Drain "Miller" Charge | $Q_{\rm gd}$ | | - | 3 | - | |

| DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS | | | | | | | |
|--|-----------------|--|------|------|------|------|--|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit | |
| Drain-Source Diode Forward Voltage | V_{SD} | $V_{GS} = 0V, I_{S} = 1A$ | - | - | 1.2 | V | |
| Body Diode Reverse Recovery Time | t _{rr} | 1 124 41/44 E004/ T 2500 | - | - | 23 | ns | |
| Body Diode Reverse Recovery Charge | Q_{rr} | I_F =13A, dl/dt=500A/ μ s, T_J =25°C | - | - | 105 | nC | |

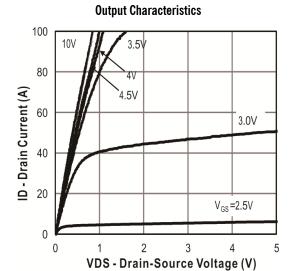
Notes:

- Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 in still

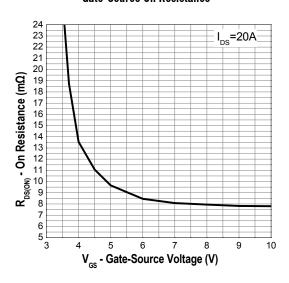




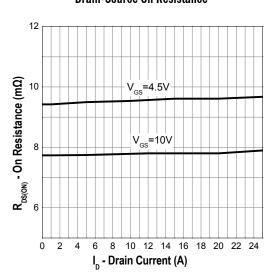
Typical Operating Characteristics



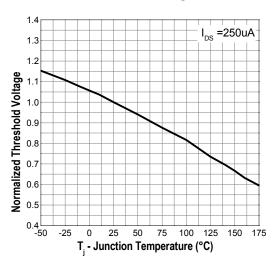
Gate-Source On Resistance



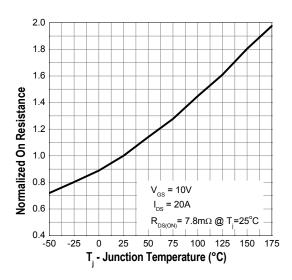
Drain-Source On Resistance



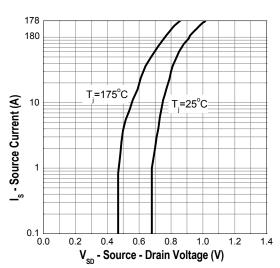
Gate Threshold Voltage



Drain-Source On Resistance



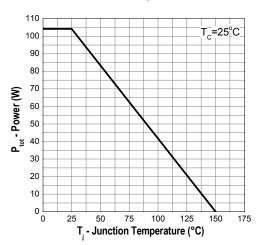
Source-Drain Diode Forward



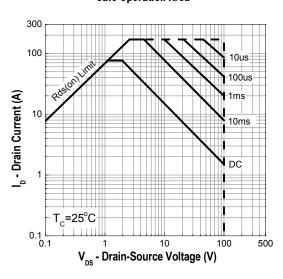


Typical Operating Characteristics (Cont.)

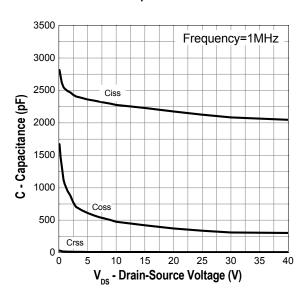




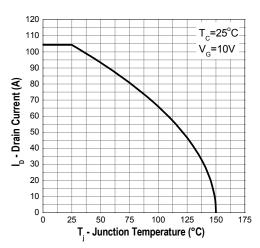
Safe Operation Area



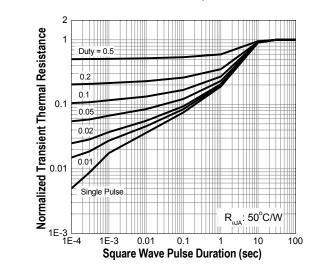
Capacitance



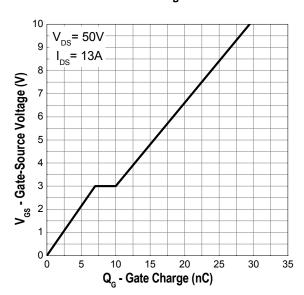
Drain Current



Transient Thermal Impedance



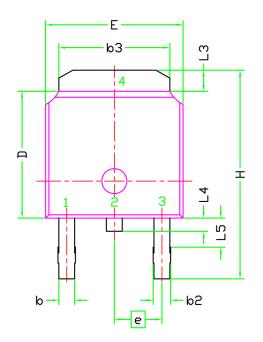
Gate Charge

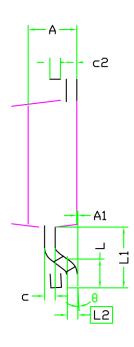


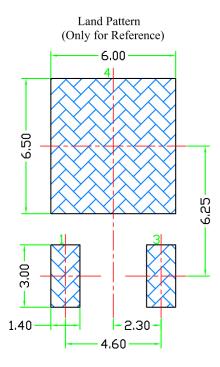


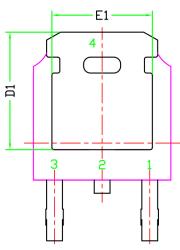
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Outline Dimension

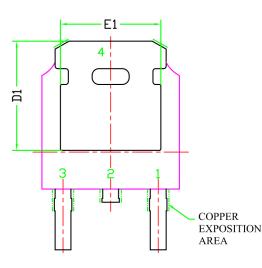












MATRIX L/F

| SYMBUL | DIMENS: | | REQMTS |
|----------|---------|---------|--------|
| 2 I MRUL | MIN | NDM | MAX |
| E | 6.40 | 6.60 | 6.731 |
| L | 1.40 | 1.52 | 1.77 |
| L1 L2 | 2 | .743 RI | EF |
| | 0. | .508 BS | C |
| L3 | 0.89 | | 1.27 |
| L4 | 0.64 | | 1.01 |
| L5 | | | |
| D | 6.00 | 6.10 | 6.223 |
| Ι | 9.40 | 10.00 | 10.40 |
| م | 0.64 | 0.76 | 0.88 |
| 20 | 0.77 | 0.84 | 1.14 |
| b3 | 5.21 | 5.34 | 5.46 |
| ω | 2. | 286 BS | C |
| Α | 2.20 | 2.30 | 2.38 |
| A1 | 0 | | 0.127 |
| U | 0.46 | 0.50 | 0.60 |
| ر م | 0.46 | 0.50 | 0.58 |
| D1 | 5,21 | | |
| E1 | 4.40 | | |
| θ | 0* | | 10° |

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- Dimension "b" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.10 mm Total In Excess Of "b" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.



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